

Weebit Nano and Leti file two new patents optimising ReRAM performance

14 June 2019 – Weebit Nano (ASX: WBT), the Israel-based semiconductor company seeking to develop and commercialise the next generation of memory technology, and its development partner Leti, the French research institute recognised as a global leader in the field of micro-electronics, have filed two new patents for Weebit's Silicon Oxide (SiOx) ReRAM technology.

Weebit and Leti's new patents relate to methods for optimising the performance of ReRAM memory cells by adjusting the manufacturability based on electrical measurements. One patent outlines a general methodology used to achieve the highest electrical performance of ReRAM cells while the other is the specification of that methodology. Identifying the unique SiOx device specification and manufacturing method enhances the commercial viability of Weebit's technology, and therefore reduces manufacturing costs and allows for more flexible manufacturing capability.

Coby Hanoch, CEO of Weebit Nano, said: "As we move closer to productisation, we are constantly looking for ways to optimise our SiOx ReRAM technology. Our close collaboration with Leti has enabled us to make significant progress and technological breakthroughs, such as the ones covered by these two patents. The precise specification of the optimisation process allows us to push the boundaries of ReRAM technology even further and places us at the forefront of the ReRAM industry."

"While we continue to work on optimising parameters of Weebit's ReRAM technology and responding to feedback from potential customers, the latest advancement significantly enhances our manufacturing process and capability ahead of the move to a production fab."

For further information, contact:

Investors

Eric Kuret Market Eye

P: +61 3 9591 8904

E: eric.kuret@marketeye.com.au

Media

Tristan Everett Market Eye

P: +61 3 9591 8905

E: tristan.everett@marketeye.com.au



About Weebit Nano Limited

Weebit Nano is a leader in the development of next generation computer memory technology, and plans to become the new industry standard in this space. Its goal is to address the growing need for a significantly higher performance and lower power computer memory technology. Weebit Nano's ReRAM technology is based on fab-friendly Silicon Oxide, allowing the company to rapidly execute, without the need for special equipment or preparations. The company secured several patents to ensure optimal commercial and legal protection for its ground-breaking technology.

Weebit Nano's technology enables a quantum leap, allowing semiconductor memory elements to be significantly cheaper, faster, more reliable and more energy efficient than the existing Flash technology. Weebit Nano has signed an R&D agreement with Leti, an R&D institute that specialises in nanotechnologies, to further develop SiOx ReRAM technology.

For more information please visit: http://www.weebit-nano.com/